**Product data sheet** 

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- Trench MOSFET technology
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C	-	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C	-	-	22	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C	-	-	19	W
Static chara	acteristics		'	'		<u> </u>
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 7.2 \text{ A}; T_j = 25 \text{ °C}$	-	16	22	mΩ



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15/376	D
2	D	drain		
3	G	gate	2 5	G ✓ ↓ ↓ ★ \
4	S	source	3 8 4	\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	s
7	D	drain		017aaa255
8	S	source		

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
BUK6D22-30E		plastic, leadless thermal enhanced ultra thin small outline package; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
BUK6D22-30E	6A

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	22	Α
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 100 °C		-	15.7	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	7.2	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	89	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	19	W
		T <sub>amb</sub> = 25 °C	[1]	-	2	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	diode		'			
Is	source current	T <sub>sp</sub> = 25 °C		-	19	Α
		T <sub>amb</sub> = 25 °C	[1]	-	2	Α
I <sub>SM</sub>	peak source current	single pulse; $t_p \le 10 \mu s$ ; $T_{sp} = 25 °C$		-	75	Α
ESD maximu	m rating		'		'	
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	2000	V
Avalanche ru	ggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.17 A; DUT in avalanche (unclamped)		-	17.4	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Measured between all pins.

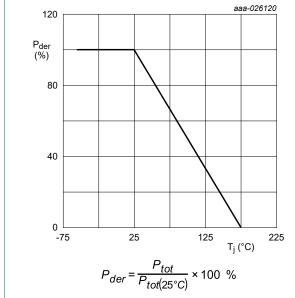


Fig. 1. Normalized total power dissipation as a function of junction temperature

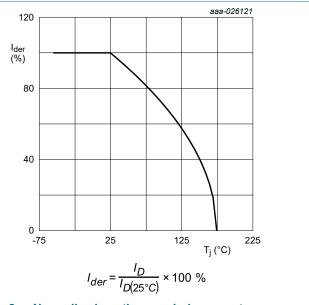


Fig. 2. Normalized continuous drain current as a function of junction temperature

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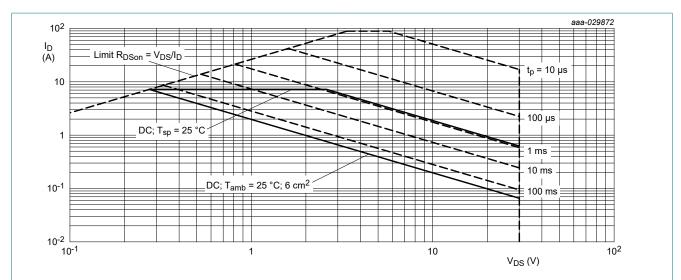


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	4	8	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

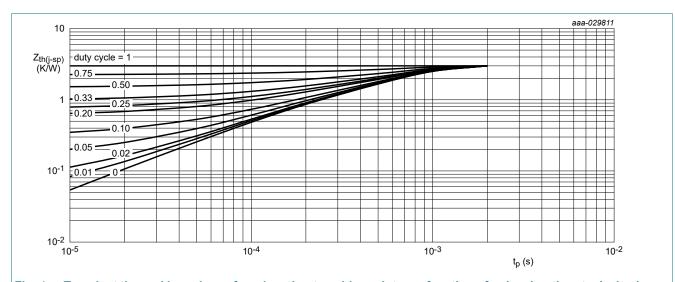


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration; typical values

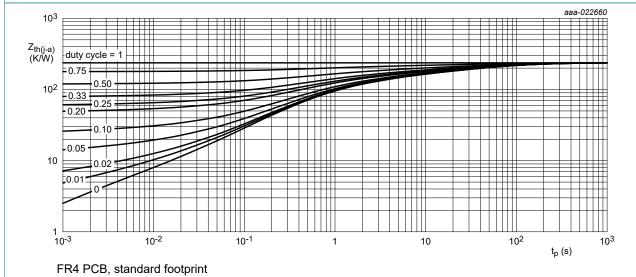


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	20	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-2	μΑ
Doon	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 7.2 A; T <sub>j</sub> = 25 °C	-	16	22	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 7.2 A; T <sub>j</sub> = 175 °C	-	28	38	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 6.2 \text{ A}; T_j = 25 \text{ °C}$	-	22	30	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	24	-	S
$R_{G}$	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 7.2 A; V <sub>GS</sub> = 10 V;	-	9.5	14	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
$Q_{GD}$	gate-drain charge		-	2.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	440	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	110	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	75	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 7.2 A; V <sub>GS</sub> = 10 V;	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	18	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	15	-	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-dra	in diode		1			
V <sub>SD</sub>	source-drain voltage	$I_S = 2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 2 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	11	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V; T <sub>j</sub> = 25 °C	-	4	-	nC

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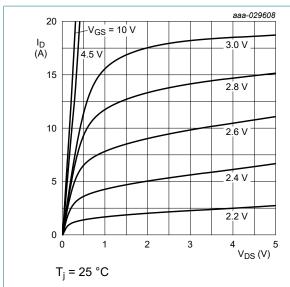


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

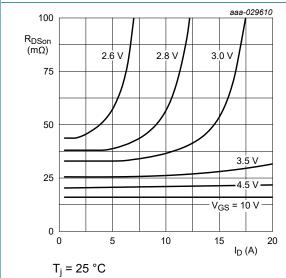


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

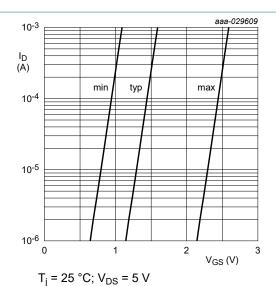


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

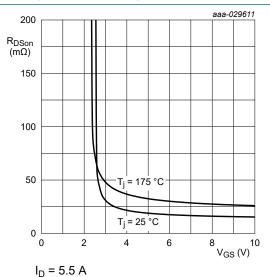


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, N-channel Trench MOSFET

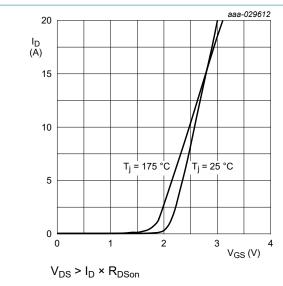


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

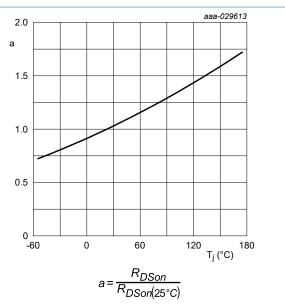


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

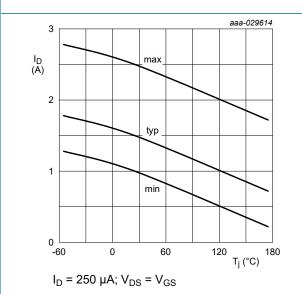


Fig. 12. Gate-source threshold voltage as a function of junction temperature

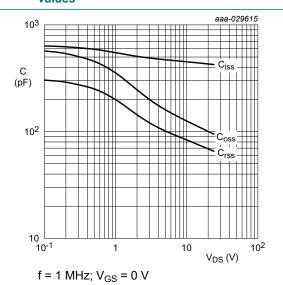


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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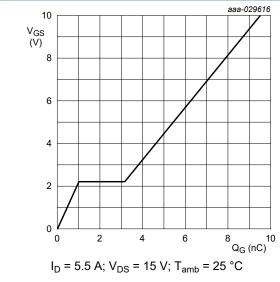


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

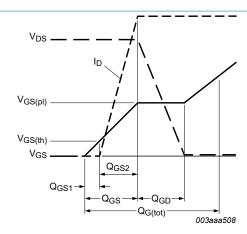


Fig. 15. Gate charge waveform definitions

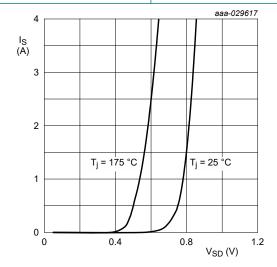
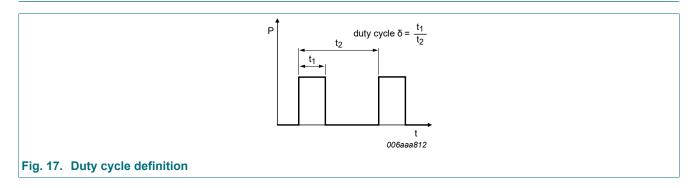


Fig. 16. Source current as a function of source-drain voltage; typical values

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## 11. Test information



### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 12. Package outline

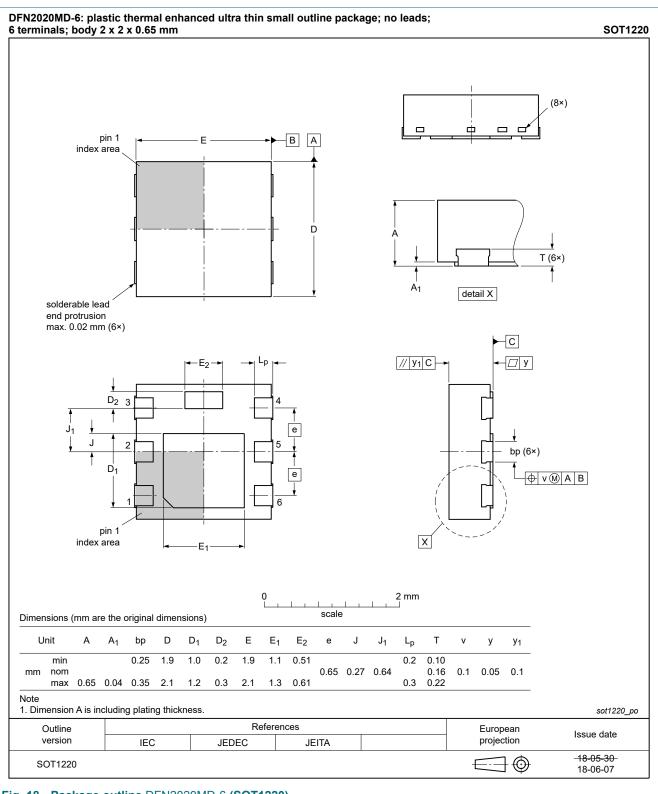
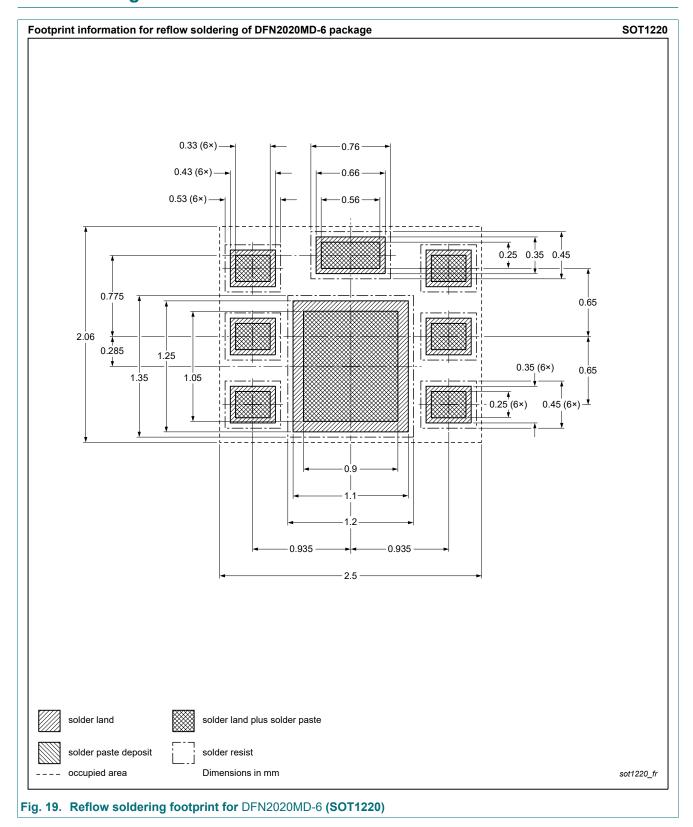


Fig. 18. Package outline DFN2020MD-6 (SOT1220)

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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BUK6D22-30E v.1	20190410	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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